

Plan for production  
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MITSUBISHI SEMICONDUCTOR <GaAs FET>

**MGFC36V7177**

**7.1~7.7GHz BAND 4W INTERNALLY MATCHED GaAs FET**

## DESCRIPTION

The MGFC36V7177 is an internally impedance-matched GaAs power FET especially designed for use in 7.1 ~ 7.7 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

## FEATURES

- Class A operation
- Internally matched to 50Ω system
- High output power  
 $P_{1dB} = 4 \text{ W (TYP) @ 7.1 ~ 7.7 GHz}$
- High power gain  
 $G_{LP} = 9 \text{ dB (TYP) @ 7.1 ~ 7.7 GHz}$
- High power added efficiency  
 $\eta_{add} = 30\% \text{ (TYP) @ 7.1 ~ 7.7 GHz, } P_{1dB}$
- Hermetically sealed metal-ceramic package

## APPLICATION

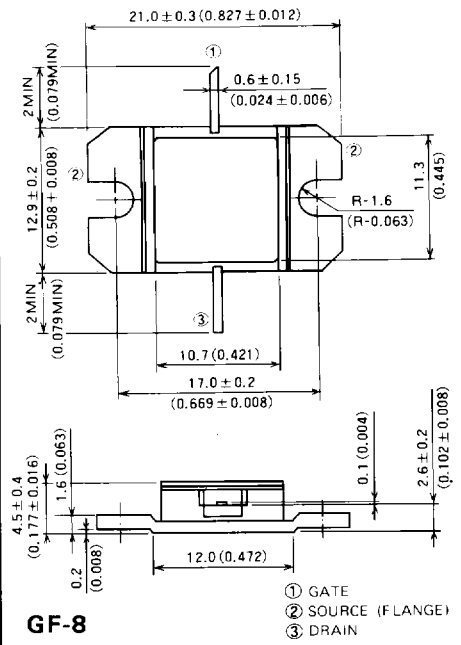
Item-01: 7.1~7.7 GHz band power amplifier  
Item-51: Digital radio communication

## QUALITY GRADE

- IG

## OUTLINE DRAWING

Unit: millimeters (inches)



## RECOMMENDED BIAS CONDITIONS

- $V_{DS} = 10\text{V}$
- $I_D = 1.2\text{A}$
- $R_g = 100\Omega$
- Refer Bias Procedure

## ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Ratings	Unit
$V_{GDO}$	Gate to drain voltage	-15	V
$V_{GSO}$	Gate to source voltage	-15	V
$I_D$	Drain current	2.8	A
$I_{GR}$	Reverse gate current	-10	mA
$I_{GF}$	Forward gate current	+21	mA
$P_T$	Total power dissipation *1	25	W
$T_{Ch}$	Channel temperature	175	$^\circ\text{C}$
$T_{Stg}$	Storage temperature	-65 ~ +175	$^\circ\text{C}$

\*1:  $T_c = 25^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

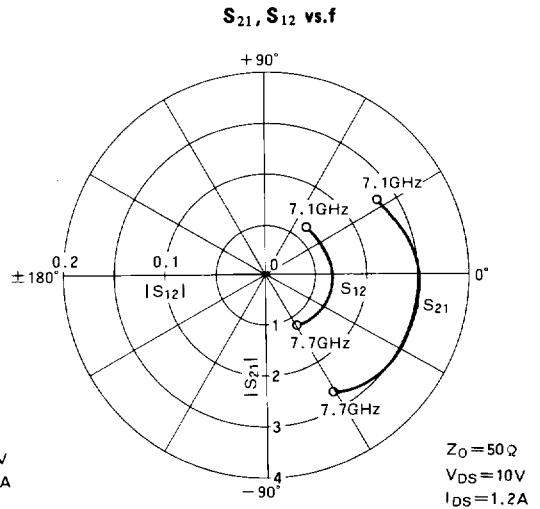
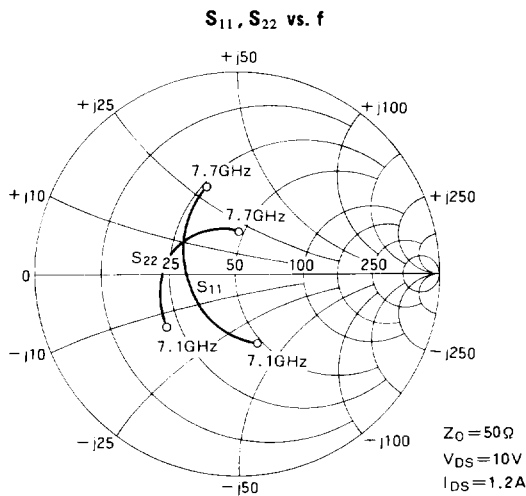
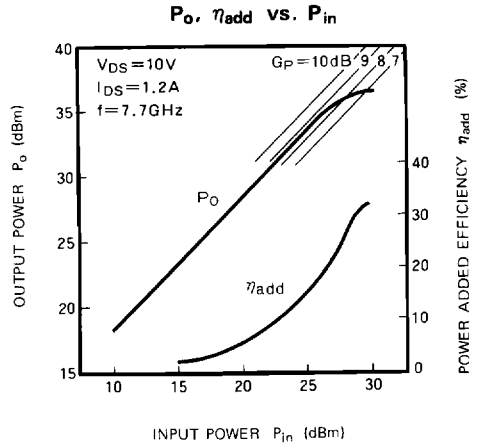
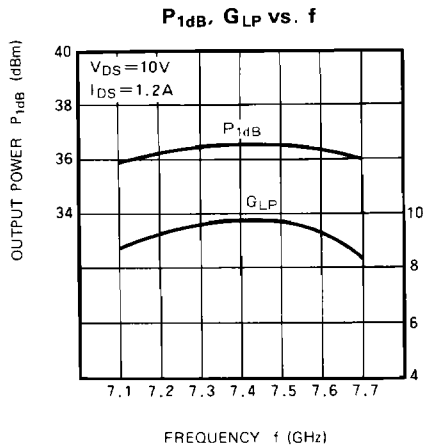
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$I_{DSS}$	Saturated drain current	$V_{DS} = 3\text{V}, V_{GS} = 0\text{V}$	—	2.0	2.8	A
$g_m$	Transconductance	$V_{DS} = 3\text{V}, I_D = 1.1\text{A}$	—	1.0	—	S
$V_{GS(off)}$	Gate to source cut-off voltage	$V_{DS} = 3\text{V}, I_D = 10\text{mA}$	-2	-3	-4	V
$P_{1dB}$	Output power at 1dB gain compression	$V_{DS} = 10\text{V}, I_D = 1.2\text{A}, f = 7.1 \sim 7.7\text{GHz}$	35	36	—	dBm
$G_{LP}$	Linear power gain		8	9	—	dB
$I_D$	Drain current		—	1.1	1.4	A
$\eta_{add}$	Power added efficiency		—	30	—	%
$IM_3$	3rd order IM distortion *1		-42	-45	—	dBc
$R_{th(ch-c)}$	Thermal resistance *2	$\Delta V_I$ method	—	—	6	$^\circ\text{C/W}$

\*1: Item-51, 2-tone test  $P_O = 25 \text{ dBm}$  Single Carrier Level  $\Delta f = 10 \text{ MHz}$

\*2: Channel to case

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**TYPICAL CHARACTERISTICS (Ta = 25°C)**



**S PARAMETERS (Ta = 25°C, V<sub>DS</sub> = 10V, I<sub>DS</sub> = 1.2A)**

f (GHz)	S Parameters (TYP.)							
	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
7.1	0.34	-77	2.65	32	0.061	42	0.46	-145
7.2	0.28	-105	2.87	17	0.062	24	0.41	-161
7.3	0.25	-139	3.02	2	0.064	8	0.38	178
7.4	0.27	180	3.06	-16	0.064	-11	0.33	159
7.5	0.33	148	3.00	-32	0.066	-28	0.28	135
7.6	0.38	126	2.90	-47	0.062	-43	0.24	114
7.7	0.46	109	2.66	-59	0.059	-58	0.22	93